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LIST OF DOCUMENTS CITED BY APPLICANT
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APPLICANT

M. ISHIBASHI et al

FILING DATE

January 18, 2002

GROUP

U.S. PATENT DOCUMENTS

* EXAMINER INITIAL		DOCUMENT	DATE	NAME	CLASS	SUBCLASS	FILING DATE (If Appropriate)
P/K	AA	5,666,190	09/09/97	Quate et al			
P/K	AB	5,049,461	09/17/91	Arnett et al			
P/K	AC	5,546,375	8/13/96	Shimada et al			
P/K	AD	5,793,040	08/11/98	Oguchi et al			
P/K	AE	5,546,374	08/13/96	Kuroda et al			
P/K	AF	5,536,988	07/16/96	Zhang et al			
P/K	AG	5,431,055	07/11/95	Takata et al			
P/K	AH	5,150,392	09/22/92	Hohn et al			
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AL						<input type="checkbox"/>	<input type="checkbox"/>
	AM						<input type="checkbox"/>	<input type="checkbox"/>
	AN						<input type="checkbox"/>	<input type="checkbox"/>
	AO						<input type="checkbox"/>	<input type="checkbox"/>
	AP						<input type="checkbox"/>	<input type="checkbox"/>

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

P/K	AR	APPLIED PHYSICS LETTERS, Vol. 66, No. 6, Feb 6, 1995, "Fabrication of 0.1um metal oxide semiconductor field-effect transistors with the atomic force microscope," S.C. Minne et al, pp. 703-705.
P/K	AS	1997 SYMPOSIUM ON VLSI TECHNOLOGY, "Fabrication on 100nm pMOSFETs with Hybrid AFN/STM Lithography", Soh et al.
	AT	

EXAMINER

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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.